PRESS RELEASE

Infineon advances on 300-millimeter GaN manufacturing roadmap as leading Integrated Device Manufacturer (IDM)

Munich, Germany – 2 July 2025 – As the demand for gallium nitride (GaN) semiconductors continues to grow, Infineon Technologies AG (FSE: IFX / OTCQX: IFNNY) is poised to capitalize on this trend and solidify its position as a leading Integrated Device Manufacturer (IDM) in the GaN market. Today, the company announced that its scalable GaN manufacturing on 300-millimeter wafers is on track. With first samples available for customers as of the fourth quarter of 2025, Infineon is well-positioned to expand its customer base and reinforce its position as a leading GaN powerhouse.

As a leader in power systems, Infineon is mastering all three relevant materials: silicon (Si), silicon carbide (SiC) and gallium nitride. With higher power density, faster switching speeds, and lower power losses, GaN semiconductors enable smaller designs, reducing energy consumption and heat generation in electronic devices like smartphone chargers, industrial and humanoid robots or solar inverters.

“Our fully scaled-up 300-millimeter GaN manufacturing will allow us to deliver highest value to our customers even faster while moving towards cost parity for comparable silicon and GaN products,” said Johannes Schoiswohl, Head of GaN Business Line at Infineon. “Almost a year after the announcement of Infineon’s breakthrough in 300-millimeter GaN wafer technology, we are pleased that our transition process is well on track and that the industry has recognized the importance of Infineon’s GaN technology enabled by the strength of our IDM strategy.”

Infineon’s manufacturing strategy primarily relies on an IDM model – owning the entire semiconductor production process, from design to manufacturing and selling the final product. The company’s in-house manufacturing strategy is a key differentiator in the market providing several advantages such as high-quality, faster time-to-market as well as superior design and development flexibility. Infineon is committed to supporting its GaN customers and can scale capacity to meet their needs for reliable GaN power solutions.

Building on its technology leadership, Infineon has become the first semiconductor manufacturer to successfully develop 300-millimeter GaN power wafer technology within its existing high-volume manufacturing infrastructure. Chip production on 300-millimeter wafers is technically more advanced and significantly more efficient compared to established 200-

Public / For the Trade Press: INFXX202507-122e

Michael Burner (Headquarters)	+49 89 234 39300	michael.burner@infineon.com	**Investor Relations:**
Agnes Toan (Americas)	+1 408 250 1814	agnes.toan@infineon.com	+49 89 234 26655
Lin Zhu (Greater China)	+86 21 6101 9199	lin.zhu@infineon.com	investor.relations@infineon.com
Yasuyuki Kamiseki (Japan)	+81 3 4595 7079	yasuyuki.kamiseki@infineon.com	

millimeter wafers, as the larger wafer diameter allows 2.3 times more chips to be produced per wafer. These increased capabilities combined with Infineon's large team of GaN experts and the industry's broadest IP portfolio are needed as GaN power semiconductors are being rapidly adopted in industrial, automotive, consumer, and computing & communication applications, such as power supplies for AI systems, solar inverters, chargers and adapters or motor control systems.

Market analysts expect the GaN revenue for power applications to grow by 36 percent annually to approximately US $2.5 billion by 2030[1]. Infineon's dedicated manufacturing capacity and strong portfolio, with more than 40 new GaN products announced in the past year make the company a preferred partner for customers seeking high-quality GaN solutions.

About Infineon

Infineon Technologies AG is a global semiconductor leader in power systems and IoT. Infineon drives decarbonization and digitalization with its products and solutions. The company had around 58,060 employees worldwide (end of September 2024) and generated revenue of about €15 billion in the 2024 fiscal year (ending 30 September). Infineon is listed on the Frankfurt Stock Exchange (ticker symbol: IFX) and in the USA on the OTCQX International over-the-counter market (ticker symbol: IFNNY).

Further information is available at www.infineon.com
This press release is available online at www.infineon.com/press
Follow us: X - Facebook – LinkedIn

[1] *Yole Group; Power SiC and GaN Compound Semiconductor Market Monitor, Q1 2025*

Public / For the Trade Press: INFXX202507-122e

Michael Burner (Headquarters)	+49 89 234 39300	michael.burner@infineon.com	**Investor Relations:**
Agnes Toan (Americas)	+1 408 250 1814	agnes.toan@infineon.com	+49 89 234 26655
Lin Zhu (Greater China)	+86 21 6101 9199	lin.zhu@infineon.com	investor.relations@infineon.com
Yasuyuki Kamiseki (Japan)	+81 3 4595 7079	yasuyuki.kamiseki@infineon.com	